TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

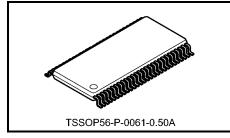
TC74VCX16721FT

Low-Voltage 20-Bit D-Type Flip-Flop with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16721FT is a high-performance CMOS 20-bit D-type flip-flop. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ \mathrm{V}.$

The TC74VCX16721FT is edge-triggered D-type flip-flop with qualified clock storage. On the positive transition of the clock (CK) input, the device provides true data at the Q outputs if the clock-enable ($\overline{\rm CKEN}$) input is low. If $\overline{\rm CKEN}$ is high, no data is stored. When the $\overline{\rm OE}$ input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.



Weight: 0.25 g (typ.)

All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: V_{CC} = 1.8 to 3.6 V
- High-speed operation: $t_{pd} = 3.5 \text{ ns (max) (VCC} = 3.0 \text{ to } 3.6 \text{ V)}$

 $t_{pd} = 4.4 \text{ ns (max) (VCC} = 2.3 \text{ to } 2.7 \text{ V)}$

 $t_{pd} = 8.8 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- Output current: IOH/IOL = ±24 mA (min) (VCC = 3.0 V)
 - $: IOH/IOL = \pm 18 \text{ mA (min) (VCC} = 2.3 \text{ V)}$

 $: I_{OH}/I_{OL} = \pm 6 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$

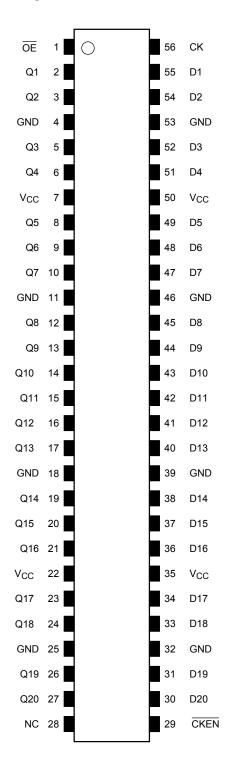
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$

Human body model ≥ ±2000 V

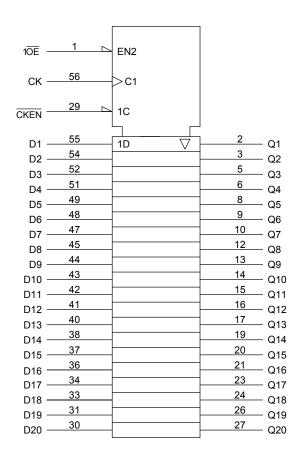
- · Package: TSSOP
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

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Pin Assignment (top view)



IEC Logic Symbol



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Truth Table (each flip-flop)

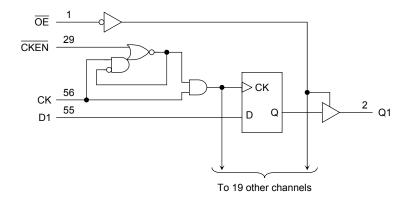
	Inputs					
ŌĒ	CKEN	CK	D	Q		
L	Н	Х	Х	Q0		
L	L		Н	Н		
L	L		L	L		
L	L	L or H	Х	Q0		
Н	Х	Х	Х	Z		

X: Don't care

Z: High impedance

Qn: No change

System Diagram





Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _C C	−0.5 to 4.6	V
DC input voltage	V_{IN}	−0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC output voltage	V_{OUT}	-0.5 to V_{CC} + 0.5	V
		(Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	lok	±50 (Note 4)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: OFF state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	1.8 to 3.6	V	
l ower supply voltage	vCC	1.2 to 3.6 (Note 2)	V	
Input voltage	V _{IN}	-0.3 to 3.6	V	
Output voltage	Vout	0 to 3.6 (Note 3)	V	
Output voltage	VOU1	0 to V _{CC} (Note 4)	v	
		±24 (Note 5)		
Output current	I _{OH} /I _{OL}	±18 (Note 6)	mA	
		±6 (Note 7)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

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Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{CC} \le 3.6$ V)

Characteri	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
lanut valtara	H-level	V _{IH}		_	2.7 to 3.6	2.0	_	V
Input voltage	L-level	V _{IL}		_	2.7 to 3.6		8.0	V
				I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	_	
	H-level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -12 mA	2.7	2.2	_	
				I _{OH} = -18 mA	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	٧
				I _{OL} = 100 μA	2.7 to 3.6	_	0.2	
I. Inval	Vol	V _{IN} = V _{IH} or V _{II}	$I_{OL} = 12 \text{ mA}$	2.7	_	0.4		
	L-level	VOL	AIM = AIH OL AIF	$I_{OL} = 18 \text{ mA}$	3.0	_	0.4	
				$I_{OL} = 24 \text{ mA}$	3.0	_	0.55	
Input leakage curre	nt	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μΑ
3 state output OEE	ctato current	la-	$V_{IN} = V_{IH}$ or V_{IL}		2.7 to 3.6		±10.0	^
3-state output OFF state current		loz	V _{OUT} = 0 to 3.6 V		2.7 10 3.0		±10.0	μА
Power-off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μΑ
Quiescent supply current		laa	V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0	
		Icc	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	_	±20.0	μΑ
Increase in I _{CC} per	input	Δlcc	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	_	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	Test Condition			Min	Max	Unit		
		Cymbol	rest dollation		V _{CC} (V)		Wida	Onne		
Input voltage	H-level	V_{IH}	-	_	2.3 to 2.7	1.6	_	V		
input voltage	L-level	V _{IL}	-	_	2.3 to 2.7	_	0.7	V		
				$I_{OH} = -100 \mu A$	2.3 to 2.7	V _{CC} - 0.2				
	H-level	VoH	VIN = VIH or VIL	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_			
				$I_{OH} = -12 \text{ mA}$	2.3	1.8	_	V		
Output voltage				$I_{OH} = -18 \text{ mA}$	2.3	1.7	_			
			$I_{OL} = 100 \ \mu A$	2.3 to 2.7	_	0.2				
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH} \ or \ V_{IL}$	$I_{OL} = 12 \text{ mA}$	2.3		0.4	
				I _{OL} = 18 mA	2.3	_	0.6			
Input leakage curre	nt	I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	_	±5.0	μА		
3-state output OFF state current		loz	V _{IN} = V _{IH} or V _{IL}		0.04-0.7		. 10.0	^		
			V _{OUT} = 0 to 3.6 V		2.3 to 2.7		±10.0	μА		
Power-off leakage of	current	l _{OFF}	V_{IN} , $V_{OUT} = 0$ to 3.6 V		0		10.0	μΑ		
Quiescent supply current		l	$V_{IN} = V_{CC}$ or GND		2.3 to 2.7	_	20.0	μА		
Quiescent supply co	ariciit	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3 to 2.7		±20.0	μΛ		



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V $_{CC}$ < 2.3 V)

Characteri	stics	Symbol	Test Condition			Min	Max	Unit
		-			V _{CC} (V)			
Input voltage	H-level	V _{IH}	_	_	1.8 to 2.3	$\begin{array}{c} 0.7 \times \\ V_{CC} \end{array}$	_	V
input voitage	L-level	V _{IL}	_	_	1.8 to 2.3	_	0.2 × V _{CC}	V
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{II}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage		J		$I_{OH} = -6 \text{ mA}$	1.8	1.4	_	V
	L-level	VOI	V _{IN} = V _{IH} or V _{II}	I _{OL} = 100 μA	1.8	_	0.2	
	L-level	VOL	AIN = AIH OL AIL	I _{OL} = 6 mA	1.8	_	0.3	
Input leakage curre	nt	I _{IN}	$V_{IN} = 0$ to 3.6 V		1.8	_	±5.0	μΑ
3-state output OFF	state current	loz	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	_	±10.0	μА
Power-off leakage of	current	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μΑ
Quiescent supply current		Icc	V _{IN} = V _{CC} or GND		1.8	_	20.0	μА
		100	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μΛ



AC Characteristics (Ta = –40 to 85°C, input: t_{r} = t_{f} = 2.0 ns, C_{L} = 30 pF, R_{L} = 500 Ω) (Note 1)

Characteristics	Symbol	Test Condition		Min	Max	Unit
			V _{CC} (V)			
			1.8	100	_	
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250	_	
Propagation delay time	t		1.8	1.5	8.8	
(CK-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	1.0	4.4	ns
(CK-Q)	tpHL		3.3 ± 0.3	8.0	3.5	
	+		1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	1.0	4.9	ns
	t _{pZH}		3.3 ± 0.3	8.0	3.8	
		Figure 1, Figure 3	1.8	1.5	7.6	
3-state output disable time	t _{pLZ}		2.5 ± 0.2	1.0	4.2	ns
	t _{pHZ}		3.3 ± 0.3	0.8	3.7	
NA!		tw (H) figure 1, Figure 2	1.8	4.0	_	
Minimum pulse width (CK)	` '		2.5 ± 0.2	1.5	_	ns
(CK)	tW (L)		3.3 ± 0.3	1.5	_	
Minimum actual time			1.8	2.5	_	
Minimum setup time (D, CKEN)	ts	Figure 1, Figure 2, Figure 4	2.5 ± 0.2	1.5	_	ns
(D, CKEN)			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time (D, CKEN)	t _h	Figure 1, Figure 2, Figure 4	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
	,		1.8	_	0.5	ns
Output to output skew	t _{osLH}	(Note 2)	2.5 ± 0.2	_	0.5	
	tosHL		3.3 ± 0.3	_	0.5	

Note 1: For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design. $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$



Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition		Тур.	Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	ιyp.	Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2.5	0.6	V
, 52		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	3.3	0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	1.8	-0.25	
Quiet output minimum dynamic V _{OI}	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2.5	-0.6	V
, a de		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	1.8	1.5	
Quiet output minimum dynamic V _{OH}	0	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2.5	1.9	V
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

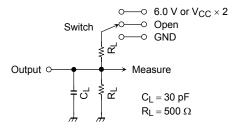
Characteristics	Symbol	Test Condition			Тур.	Unit
Gridiacteristics	ics Symbol Test Condition			V _{CC} (V)		
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note)	1.8, 2.5, 3.3	60	pF

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/20 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

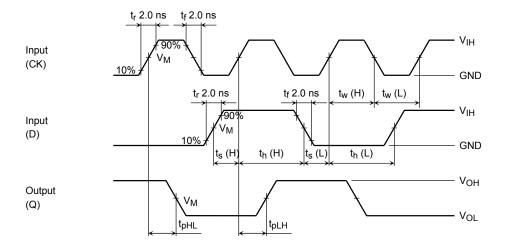


Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

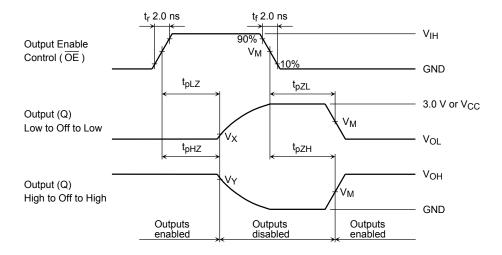


Figure 3 $\;t_{\text{pLZ}},\,t_{\text{pHZ}},\,t_{\text{pZL}},\,t_{\text{pZH}}$

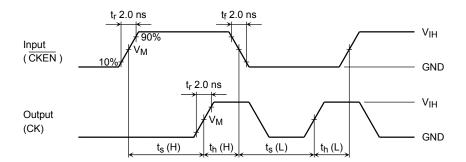


Figure 4 ts, th

Symbol		V _{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2~\textrm{V}$	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
V_{Y}	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

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Package Dimensions

TSSOP56-P-0061-0.50A Unit: mm 6.1 ± 0.1 $0.2^{\,+0.07}_{\,-0.06}$ 0.5 0.25TYP **⊕**0.1**M** 14.3MAX (0.5)14.0±0.1 0.45~0.75 1.0±0.05 0.1 ± 0.05

Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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